

IN THE CLAIMS

Cancel claims 7 and 12-23 without prejudice

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1. (Amended) A method of forming a semiconductor device, comprising:
forming a conductive bond pad over a semiconductor substrate;
forming a [dielectric] passivation layer over the conductive bond pad;
removing portions of the [dielectric] passivation layer[,], wherein removing portions of the [first dielectric] passivation layer forms a plurality of support structures that overlie the conductive bond pad, and wherein removing portions of the [dielectric] passivation layer exposes a portion of the conductive bond pad; and
forming a conductive capping layer overlying the plurality of support structures, wherein the conductive capping layer electrically contacts a portion of the conductive bond pad.

REMARKS

The specification has been amended to correct typographical errors, claim 1 has been amended to more clearly define the present invention and claims 7, and 12-23 have been cancelled without prejudice. Applicants submit the amendment does not add new matter to the current Application.

Applicants respectfully submit that claim 2 is not indefinite under 35 U.S.C. 112. Applicants further respectfully submit that one of ordinary skill in the art readily understands that a conductive bond pad, which includes *mostly* copper is, simply, a conductive bond pad that includes a greater atomic weight % of copper as compared to any other element within the bond pad. For example, if the conductive bond pad includes copper and aluminum, then the copper content of the *mostly* copper containing bond pad is greater than 50 atomic weight